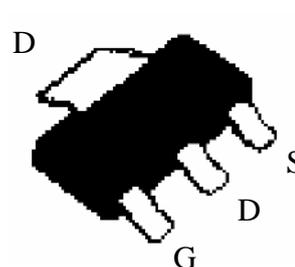


N -Channel Enhancement Mode Power MOSFET

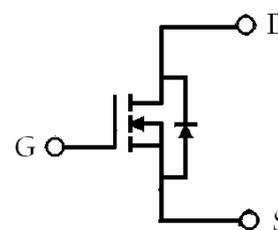
Features:

- Low Gate Charge
- Simple Drive Requirement
- RoHS compliant & Halogen-free package

SOT-223



B _V D _{SS}	60V
I _D	5.9A
R _{DSON} @ V _{GS} =10V, I _D =5A	41mΩ (typ)
R _{DSON} @ V _{GS} =4.5V, I _D =3A	46mΩ (typ)



G : Gate D : Drain
 S : Source

Ordering Information

Device	Package	Shipping
KLB60N06	SOT-223 (Pb-free lead plating and halogen-free package)	2500 pcs / tape & reel

Absolute Maximum Ratings ($T_C=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Limits	Unit	
Drain-Source Voltage	V_{DS}	60	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current @ $T_A=25^{\circ}\text{C}$, $V_{GS}=10\text{V}$	I_D	5.9	A	
Continuous Drain Current @ $T_A=100^{\circ}\text{C}$, $V_{GS}=10\text{V}$		3.7		
Pulsed Drain Current *1	I_{DM}	30		
Total Power Dissipation *2	P_d	$T_A=25^{\circ}\text{C}$	2.7	W
		$T_A=100^{\circ}\text{C}$	1.1	
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55~+150	$^{\circ}\text{C}$	

Note : *1. Pulse width limited by maximum junction temperature

*2. Surface mounted on a 1 in² pad of 2 oz. copper, $t \leq 10\text{s}$.

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{th,j-c}$	14	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-ambient, max	$R_{th,j-a}$	45 (Note)	$^{\circ}\text{C}/\text{W}$

Note : Surface mounted on a 1 in² pad of 2 oz. copper, $t \leq 10\text{s}$; $120^{\circ}\text{C}/\text{W}$ when mounted on minimum copper pad.

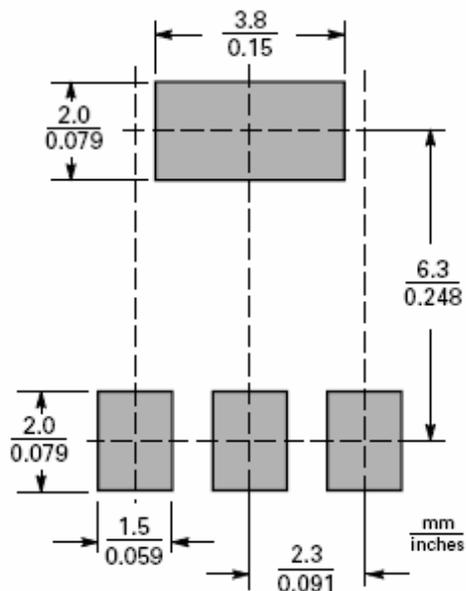
Characteristics ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	60	-	-	V	$V_{GS}=0, I_D=250\mu\text{A}$
$V_{GS(th)}$	1.0	1.8	3	V	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$
G_{FS} *1	-	9	-	S	$V_{DS}=5\text{V}, I_D=5\text{A}$
I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 20, V_{DS}=0$
I_{DSS}	-	-	1	μA	$V_{DS}=60\text{V}, V_{GS}=0$
	-	-	25	μA	$V_{DS}=48\text{V}, V_{GS}=0, T_j=70^{\circ}\text{C}$
$R_{DS(ON)}$ *1	-	41	50	$\text{m}\Omega$	$V_{GS}=10\text{V}, I_D=5\text{A}$
	-	46	60	$\text{m}\Omega$	$V_{GS}=4.5\text{V}, I_D=3\text{A}$
Dynamic					
Q_g *1, 2	-	22	-	nC	$I_D=5\text{A}, V_{DS}=48\text{V}, V_{GS}=10\text{V}$
Q_{gs} *1, 2	-	3.2	-		
Q_{gd} *1, 2	-	7.6	-		
$t_{d(ON)}$ *1, 2	-	6.4	-	ns	$V_{DS}=30\text{V}, I_D=5\text{A}, V_{GS}=10\text{V}, R_G=3.3\Omega$
t_r *1, 2	-	9	-		
$t_{d(OFF)}$ *1, 2	-	30	-		
t_f *1, 2	-	6	-		
C_{iss}	-	1128	-	pF	$V_{GS}=0\text{V}, V_{DS}=30\text{V}, f=1\text{MHz}$
C_{oss}	-	42	-		
C_{rss}	-	32	-		
R_g	-	2.5	-	Ω	$V_{GS}=15\text{mV}, V_{DS}=0, f=1\text{MHz}$

Source-Drain Diode					
I_S *1	-	-	2.3	A	
I_{SM} *3	-	-	9.2		
V_{SD} *1	-	-	1.3	V	$I_F=I_S, V_{GS}=0V$
t_{rr}	-	25	-	ns	$I_F=5A, dI_F/dt=100A/\mu s$
Q_{rr}	-	45	-	nC	

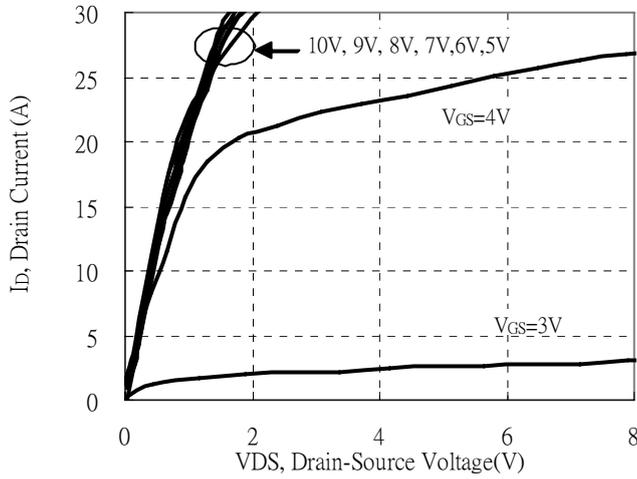
Note : *1.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
 *2.Independent of operating temperature
 *3.Pulse width limited by maximum junction temperature.

Recommended soldering footprint

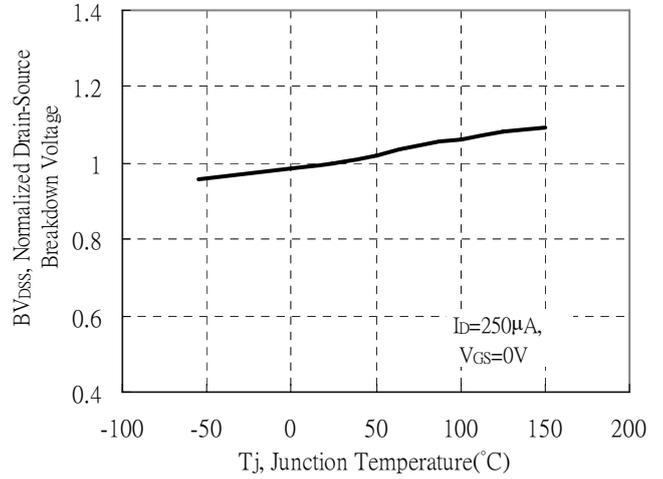


Typical Characteristics

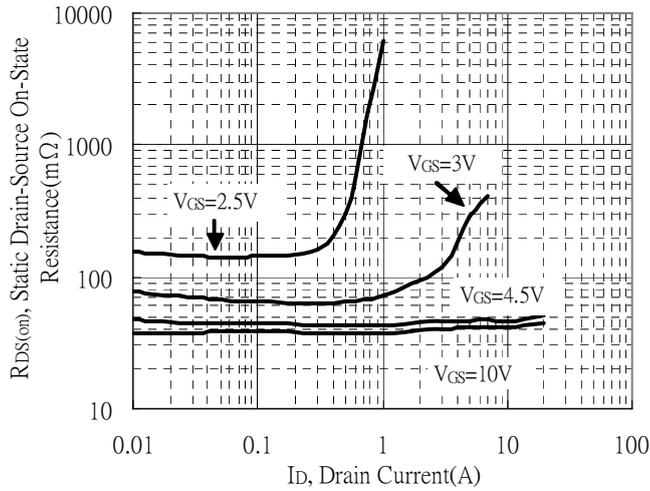
Typical Output Characteristics



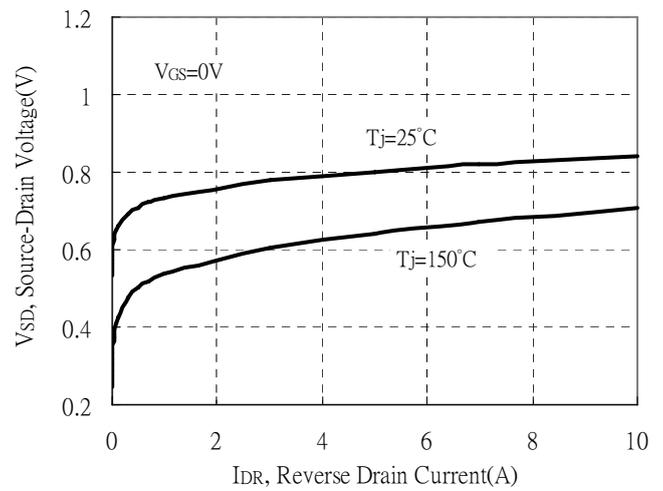
Breakdown Voltage vs Ambient Temperature



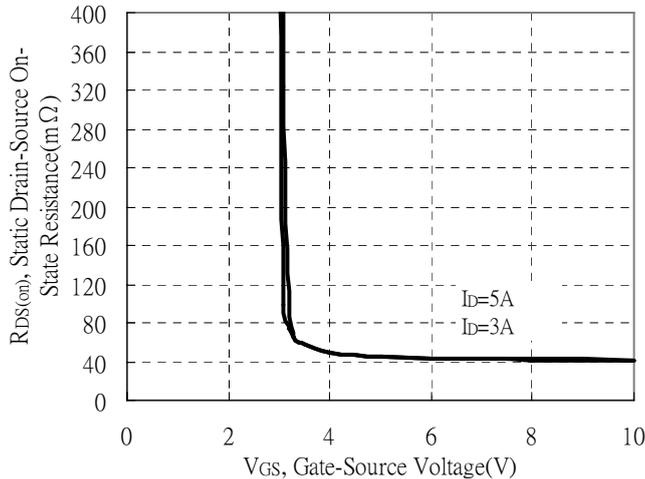
Static Drain-Source On-State resistance vs Drain Current



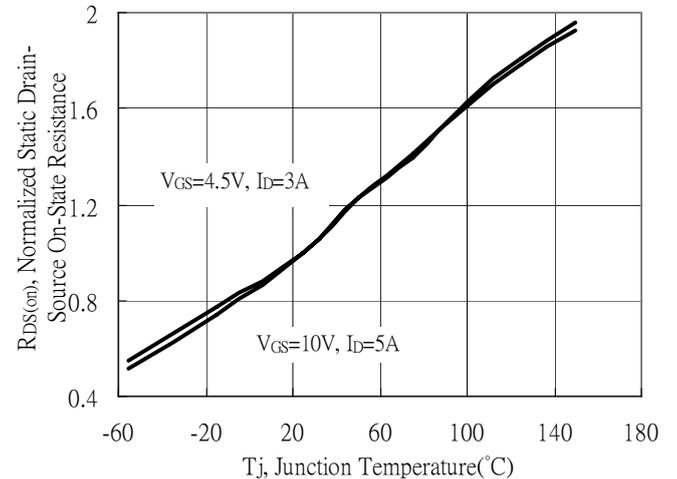
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

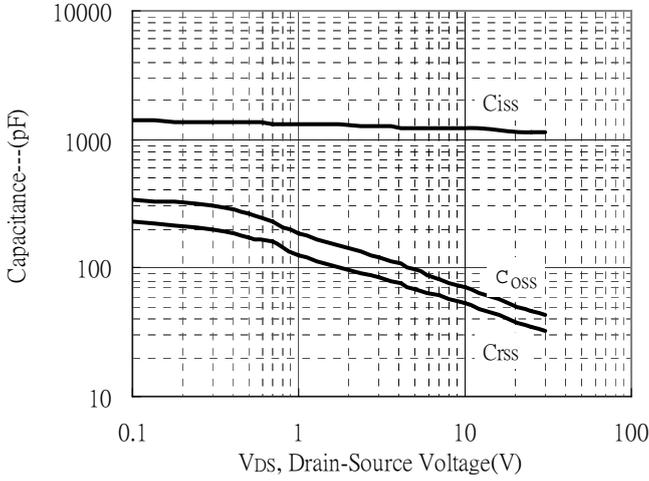


Drain-Source On-State Resistance vs Junction Temperature

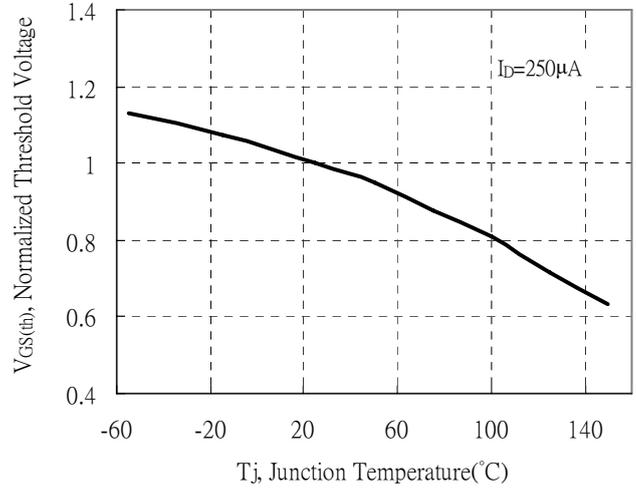


Typical Characteristics(Cont.)

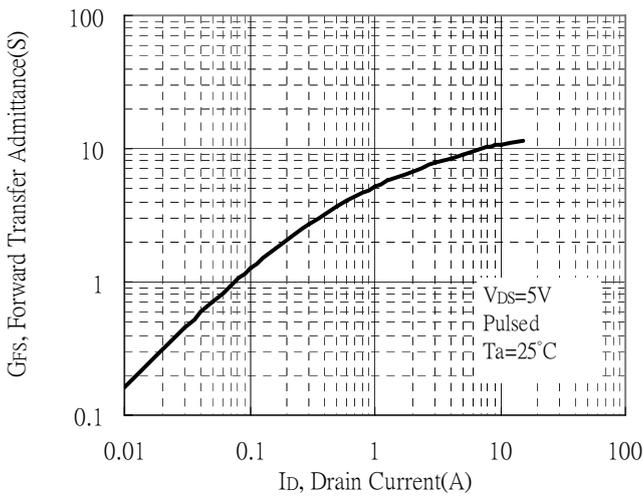
Capacitance vs Drain-to-Source Voltage



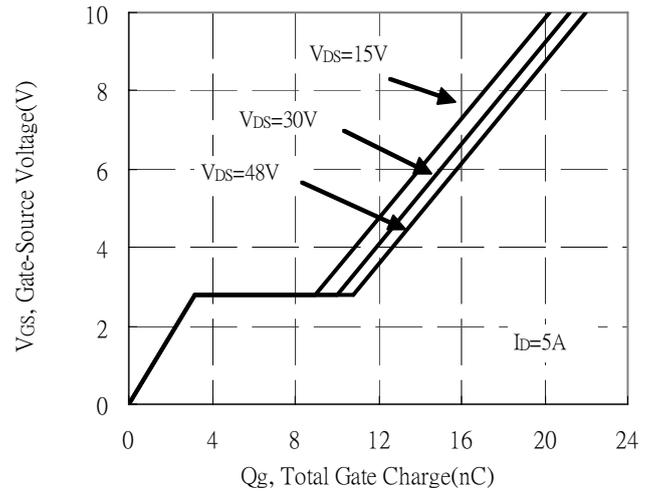
Threshold Voltage vs Junction Temperature



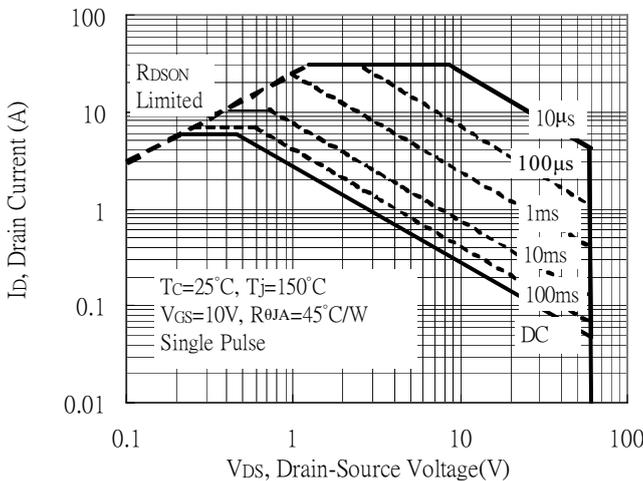
Forward Transfer Admittance vs Drain Current



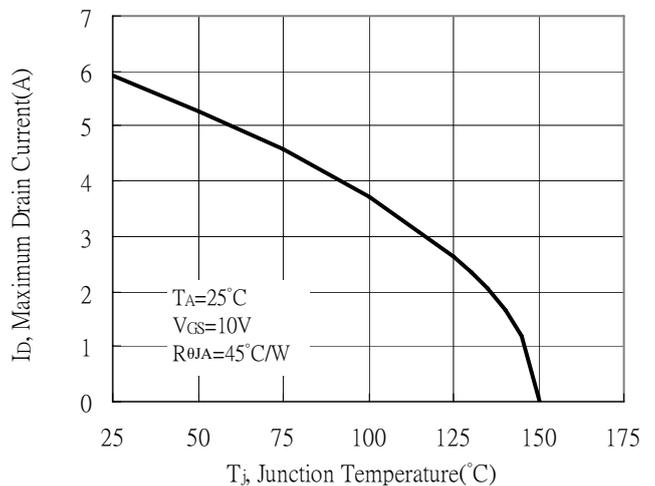
Gate Charge Characteristics



Maximum Safe Operating Area

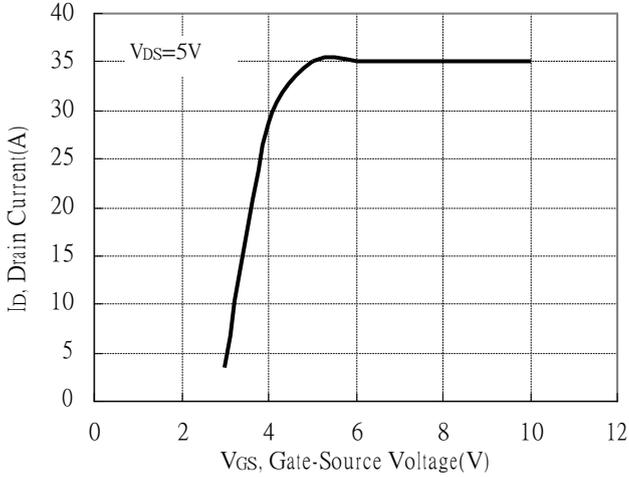


Maximum Drain Current vs Case Temperature

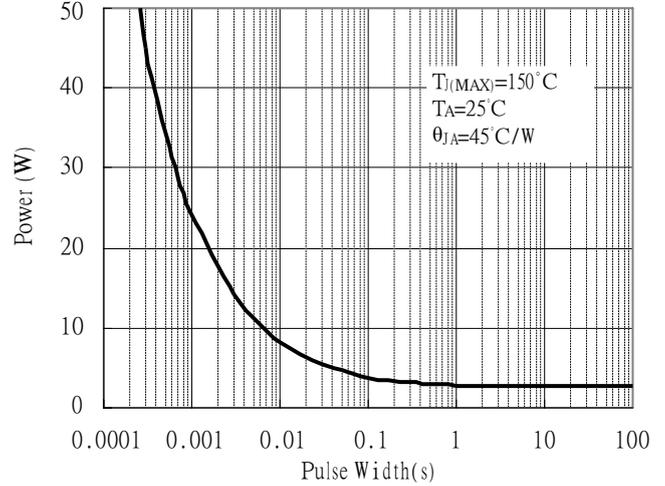


Typical Characteristics(Cont.)

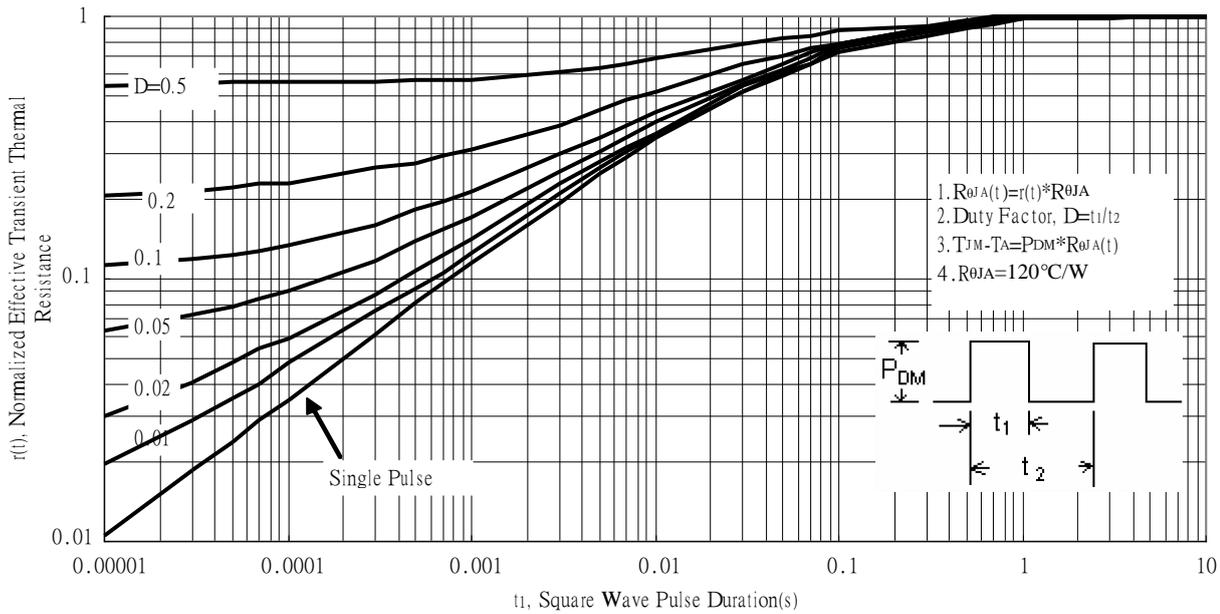
Typical Transfer Characteristics



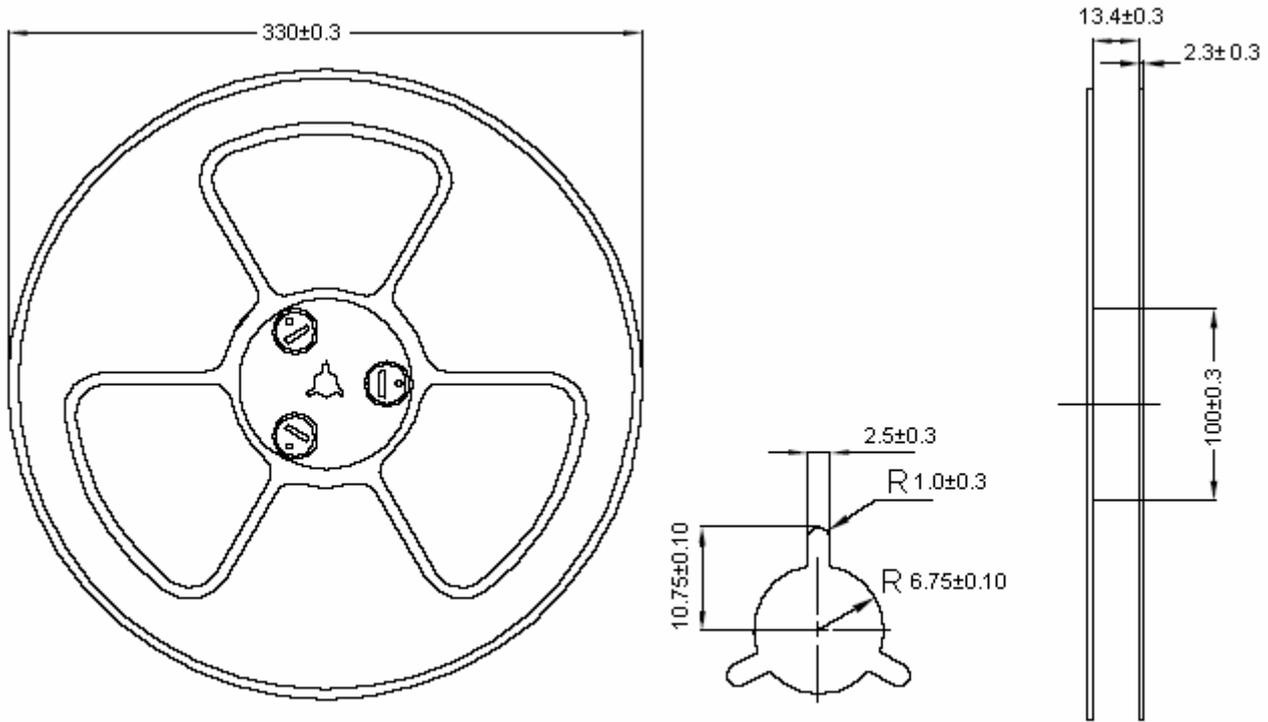
Single Pulse Power Rating, Junction to Ambient
 (Note on page 2)



Transient Thermal Response Curves



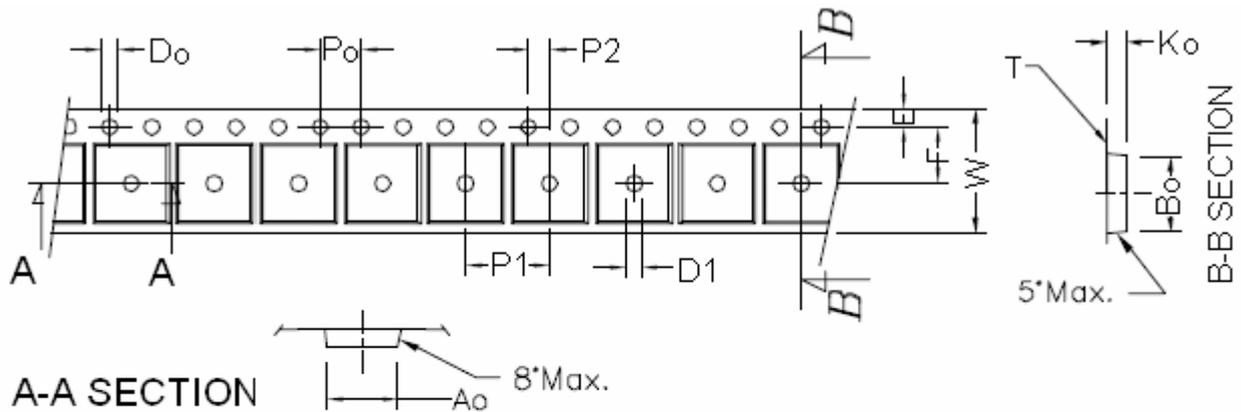
Reel Dimension



UNIT : mm

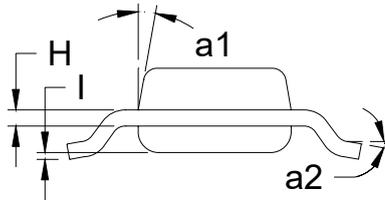
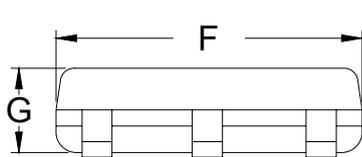
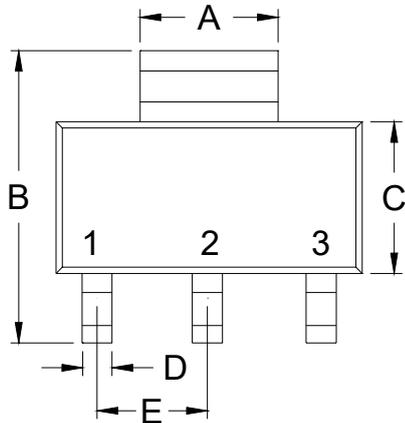
NOTE : 1. Material : Anti-static polystyrene
 2. Surface resistivity $10^9 \Omega/\text{sq}$

Carrier Tape Dimension

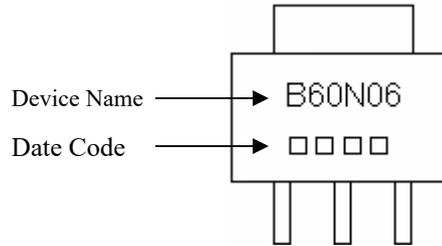


Symbol	Ao	Bo	Ko	Po	P1	P2	T
Spec	6.83±0.1	7.42±0.1	1.88±0.1	4.0±0.1	8.0±0.10	2.0±0.05	0.292±0.02
Symbol	E	F	Do	D1	W	10Po	
Spec	1.75±0.1	5.5±0.05	1.60±0.1	1.5±0.25	12 ^{+0.3} _{-0.1}	40.0±0.2	

Unit : mm



Marking:



Style: Pin 1.Gate 2.Drain 3.Source

3-Lead SOT-223 Plastic
 Surface Mounted Package

*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1142	0.1220	2.90	3.10	G	0.0551	0.0709	1.40	1.80
B	0.2638	0.2874	6.70	7.30	H	0.0098	0.0138	0.25	0.35
C	0.1299	0.1457	3.30	3.70	I	0.0008	0.0039	0.02	0.10
D	0.0236	0.0315	0.60	0.80	a1	*13°	-	*13°	-
E	*0.0906	-	*2.30	-	a2	0°	10°	0°	10°
F	0.2480	0.2638	6.30	6.70					